

INK021AAP1

High Speed Switching
Silicon N-channel MOSFET

DESCRIPTION

INK021AAP1 is a Silicon N-channel MOSFET.

This product is most suitable for use such as portable machinery, because voltage drive and low on resistance.

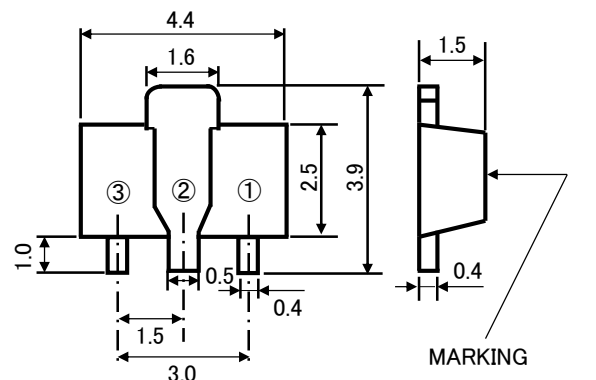
FEATURE

- Input impedance is high, and not necessary to consider a drive electric current.
- High drain current $I_D=2A$
- Drive voltage 4V
- Low on Resistance. $R_{DS(on)}=0.20\Omega$ (TYP).
- High speed switching.
- Small package for easy mounting.

FEATURE

Switching

OUTLINE DRAWING



TERMINAL CONNECTOR

JEITA: SC-62

①: GATE

JEDEC: SOT-89

②: DRAIN

③: SOURCE

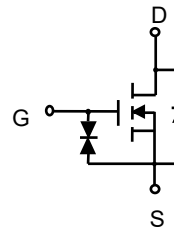
MAXIMUM RATINGS (Ta=25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V _{DSS}	100	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current(DC)	I _D	2	A
Drain Current(Pulse) (※1)	I _{DP}	8	A
Total Power Dissipation (※2)	P _D	1.5	W
Channel Temperature	T _{ch}	+150	°C
Storage Temperature	T _{stg}	-55~+150	°C

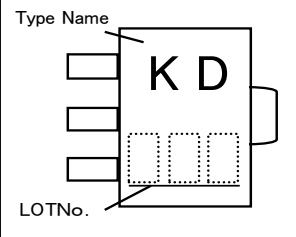
※1: Single pulse, Pw ≤ 1ms

※2: package mounted on glass-epoxy substrate (20mm × 20mm × 1mm, Cu pad 257mm²).

EQUIVALENT CIRCUIT



MARKING



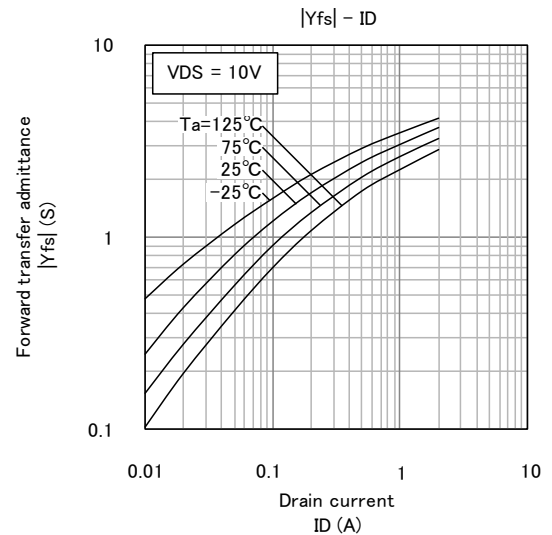
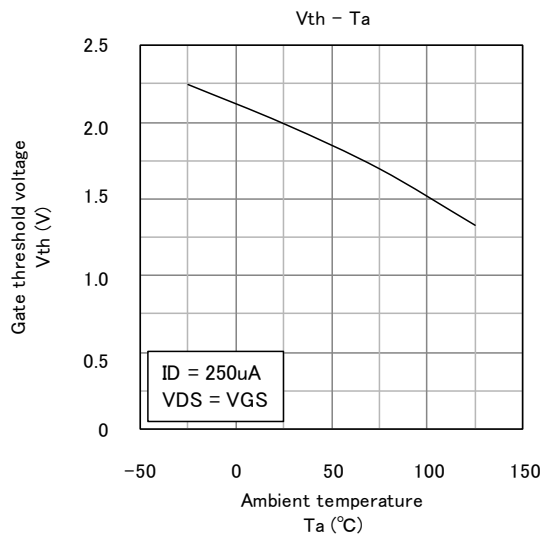
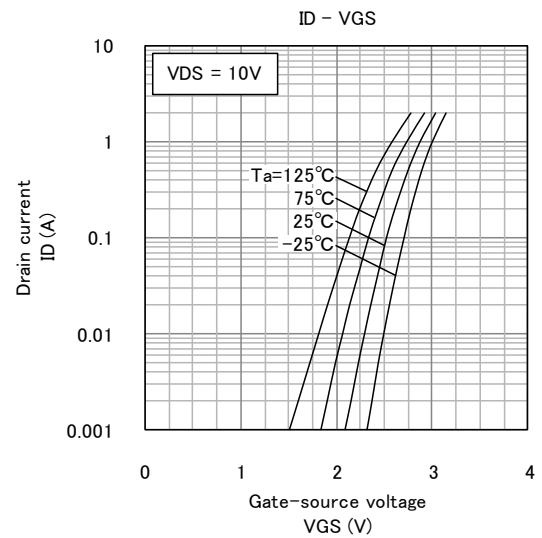
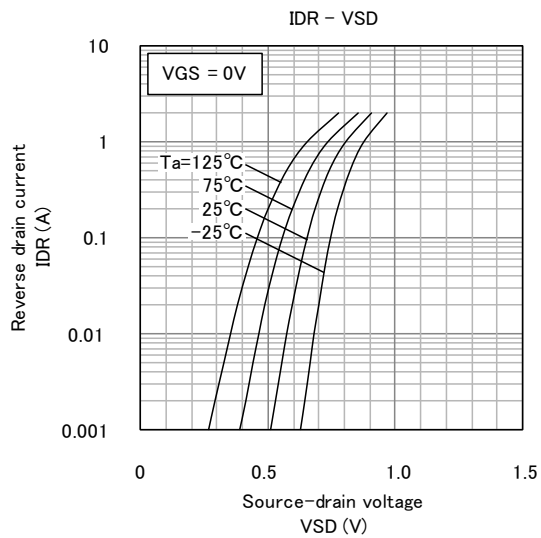
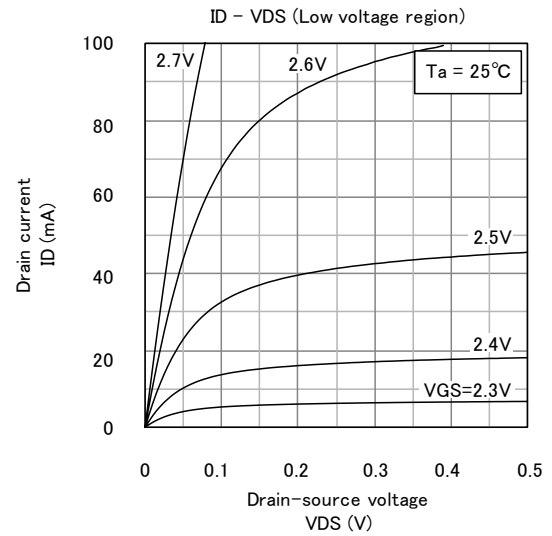
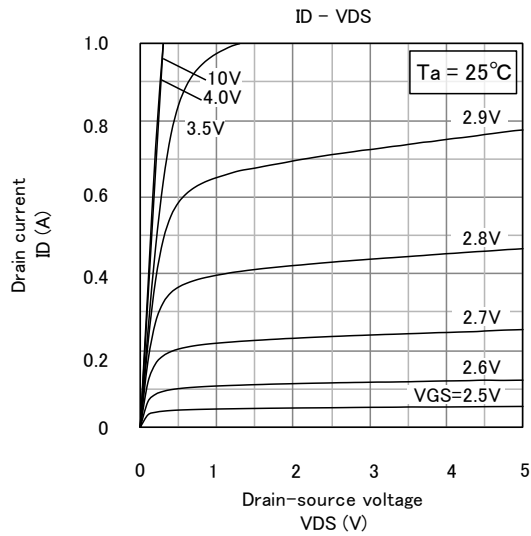
ELECTRICAL CHARACTERISTICS (Ta=25°C)

Parameter	Symbol	Test Condition	Limit			Unit
			MIN	TYP	MAX	
Drain-Source Breakdown Voltage	V(BR)DSS	I _D =100 μA, V _{GS} =0V	100	-	-	V
Gate-Source Leak current	I _{GSS}	V _{GS} =±16V, V _{DS} =0V	-	-	±10	μA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
Gate Threshold Voltage	V _{th}	I _D =250 μA, V _{DS} =V _{GS}	1.0	-	2.5	V
Forward Transfer Admittance	Y _{fs}	V _{DS} =10V, I _D =1A	-	3.0	-	S
Static Drain-Source On-State Resistance	R _{DS(ON)}	I _D =0.5A, V _{GS} =4.5V	-	0.2	-	Ω
Input Capacitance	C _{iss}	V _{DS} =10V, V _{GS} =0V, f=1MHz	-	780	-	pF
Output Capacitance	C _{oss}		-	65	-	
Switching Time	t _{on}	V _{DD} =30V, I _D =1A	-	40	-	ns
	t _{off}	V _{GS} =0~5V	-	55	-	

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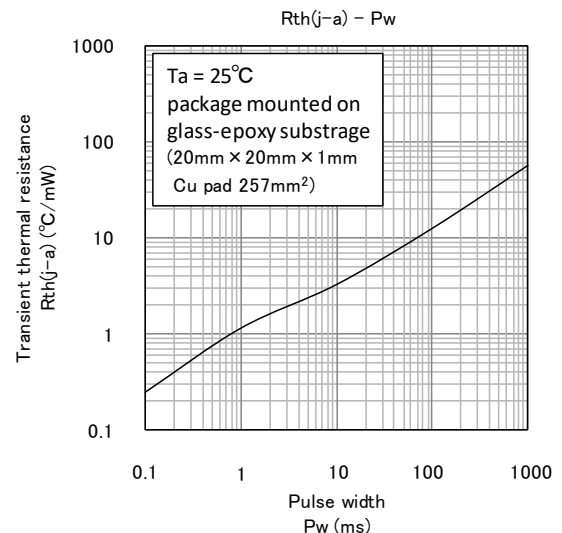
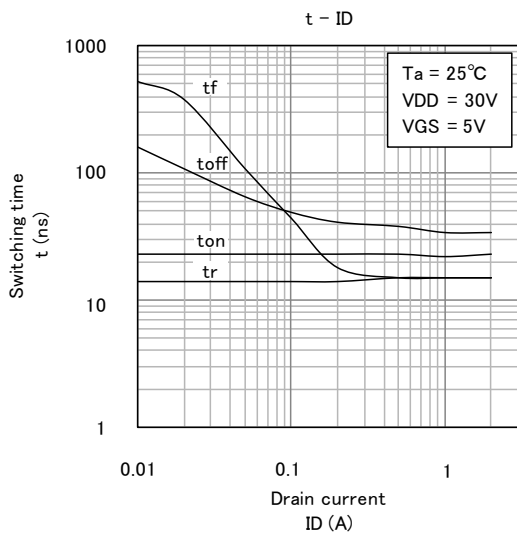
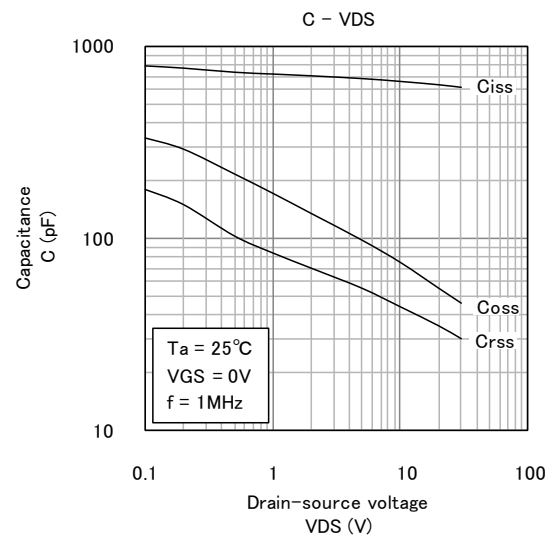
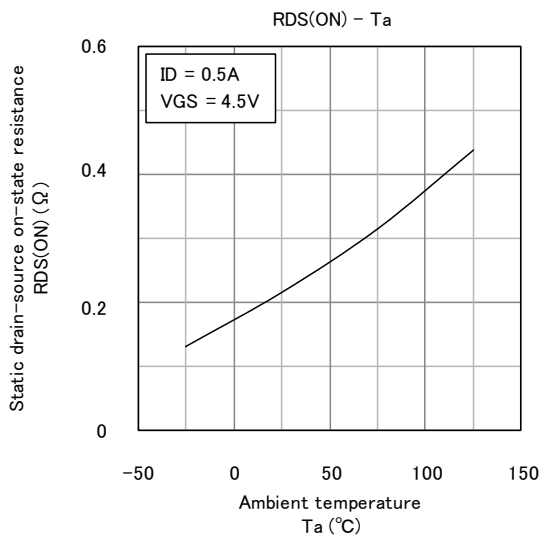
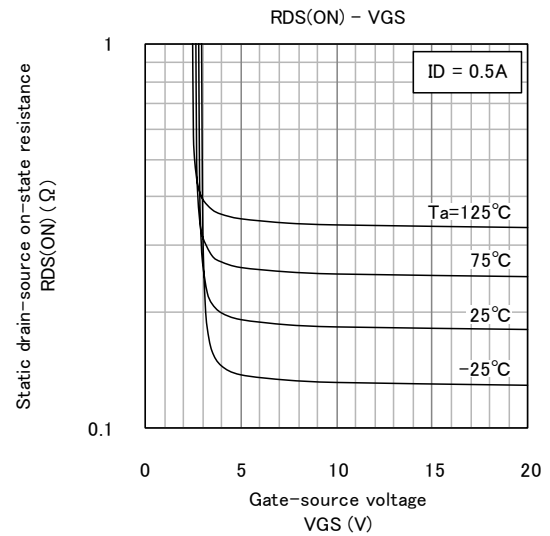
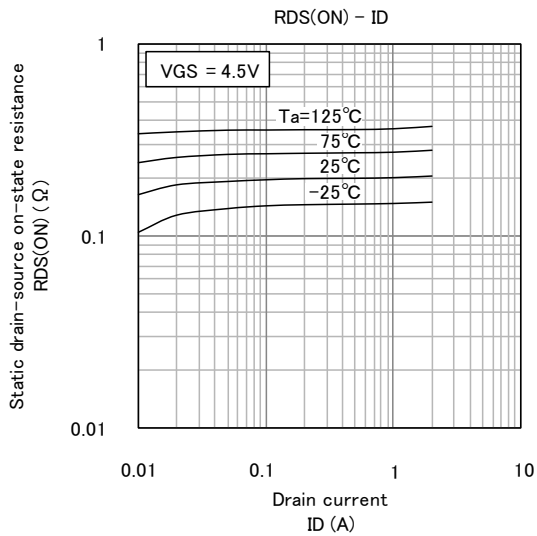
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TYPICAL CHARACTERISTICS



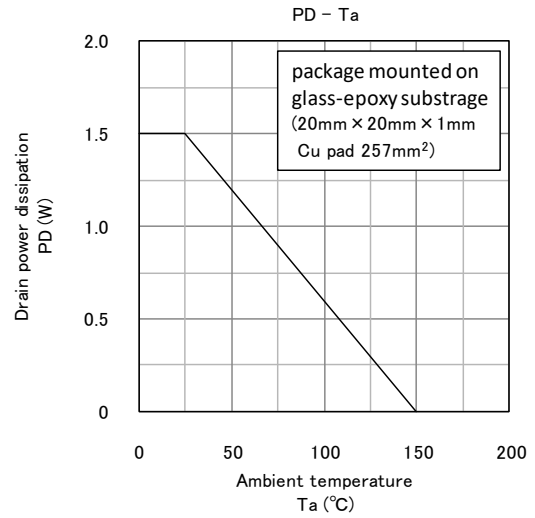
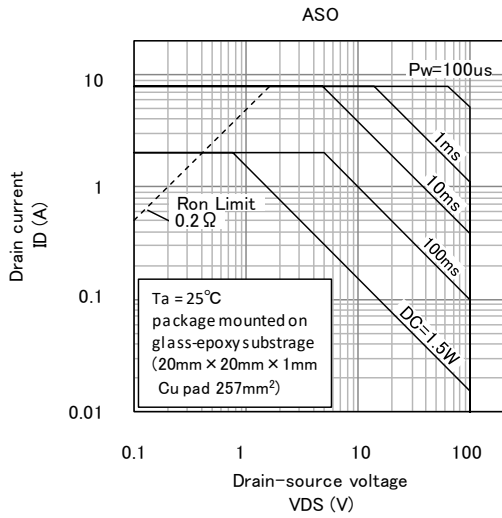
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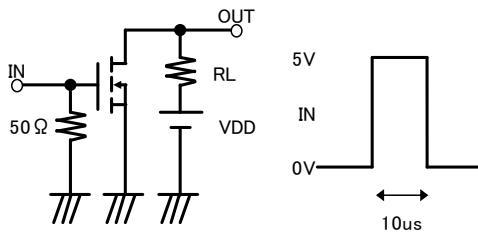


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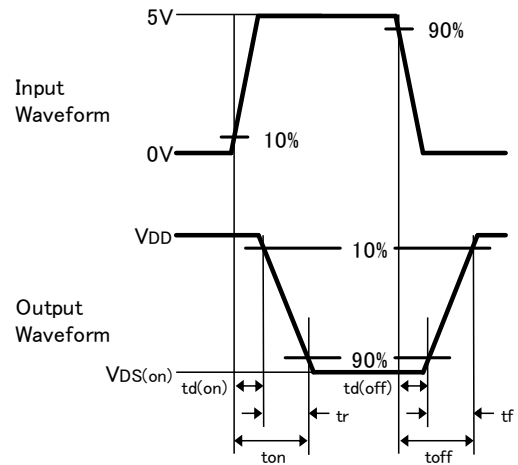
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Switching time test circuit



Duty $\leq 1\%$
Input: $t_r, t_f < 10\text{ns}$
VDD = 30V
Common source
 $T_a = 25^\circ C$



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